

CONCEPT MAP
Current Electricity

First Law: The algebraic sum of the currents meeting at a junction is zero i.e., $\Sigma I = 0$

Second Law: In a closed loop, the algebraic sum of all the potential differences is zero, i.e., $\Sigma \Delta V = 0$

Kirchoff's Law

Electric Current: The rate of flow of electric charge,
 $I = \frac{q}{t}$

Electric Power:
 $P = \frac{\text{Electric workdone}}{\text{Time taken}}$
 $P = \frac{W}{t} = VI = I^2 R = \frac{V^2}{R}$

Electric Energy:
 $E = p \times t$

Drift Velocity:
 $v_d = \frac{-eE}{m} \tau$

Mobility: It is the drift velocity per unit electric field applied
 $\mu_e = \frac{v_d}{E}$

Relation between drift velocity and current
 $I = neAv_d$

Ohm's Law: Current flowing through a conductor is directly proportional to the potential difference across its ends.
 $V = IR$

Electric Resistance: It is the obstruction posed by the conductor to the flow of electric current through it.
 $R = \rho \frac{l}{A}$

Internal Resistance of a Cell: Resistance offered by the electrolyte and electrodes of a cell when electric current flows through it.

Wheatstone Bridge : Its principle states that if four resistances P, Q, R, S are arranged to form a bridge and if the galvanometer G shows no deflection then the bridge is said to be balanced.
 $\frac{P}{Q} = \frac{R}{S}$

Metre Bridge : It is based on the principle of Wheatstone's bridge. The unknown resistance,
 $R = \frac{SI}{100-l}$

Resistance in Series:
 $R_s = R_1 + R_2 + \dots + R_n$

Resistance in Parallel:
 $\frac{1}{R_p} = \frac{1}{R_1} + \frac{1}{R_2} + \dots + \frac{1}{R_n}$

Electric Conductivity: It is the reciprocal of resistivity.

Potential Difference of a Cell: It is the potential difference between the two terminals of a cell in a closed circuit.

Emf of a Cell: It is the potential difference between the two terminals of a cell in an open circuit.

Potentiometer: Its principle is based on the facts that the fall of potential across any portion of the wire is directly proportional to the length of the wire.
 $V = Kl$

Determination of Internal Resistance of a Cell:
 $r = \left(\frac{l_1 - l_2}{l_2} \right) R$

Comparison of Emf's of Two Cells:
 $\frac{\epsilon_1}{\epsilon_2} = \frac{l_1}{l_2}$

Effect of Temperature on Resistance: The resistance of a metal conductor at a temperature $t^\circ C$ is given by $R_t = R_0(1 + \alpha t)$.

Grouping of Cells

Series Grouping:
 $I = \frac{n\epsilon}{R + nr}$
• If $R \ll nr$, then $I = \frac{\epsilon}{r}$
• If $R \gg nr$, then $I = \frac{n\epsilon}{R}$

Mixed Grouping:
 $I = \frac{n\epsilon}{R + \left(\frac{r}{m}\right)}$
current in the circuit is maximum

Parallel Grouping:
 $I = \frac{\epsilon}{R + \left(\frac{r}{m}\right)}$
• If $\frac{r}{m} \ll R$, then $I = \frac{\epsilon}{R}$
• If $\frac{r}{m} \gg R$, then $I = m \frac{\epsilon}{r}$

Symbols used:
 I = electric current
 v_d = drift velocity
 ρ = resistivity
 K = potential gradient
 q = electric charge
 μ_e = mobility
 ϵ = emf
 R_s, R_p = effective resistance
 n, m = number of cells in one row and number of rows of cells respectively
 t = time taken
 E = electric energy
 τ = time of relaxation
 l = length of the conductor
 R, r, S = resistance
 P = electric power
 E = electric field
 n_d = number density of electrons
 A = Area of cross section of conductor